

Appl. No. 09/208105
Amdt. dated Mar. 16, 2004
Reply to Office action of Oct. 27, 2003

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application.

Listing of Claims:

1-8. (Cancelled)

9. (Currently Amended) A semiconductor device comprising:

a substrate having a region irradiated with radiating rays,
crystal defects within the region irradiated,
impurity regions formed in the substrate, and
a metal wiring layer located over the entire substrate except at the metal wiring
layer being connected to each of the impurity regions, the metal wiring layer being made of a
light metal, the metal wiring layer having an opening above the region irradiated, so that wherein
radiating rays passing to the region irradiated through the opening generate the crystal defects
under the opening and so that a smaller amount of radiating rays are irradiated to regions in said
substrate except as compared with said region under the opening, the metal wiring layer being
connected to each of the impurity regions, the metal wiring layer being made of a light metal.

10. (Previously Presented) The semiconductor device in accordance with Claim 9, wherein the metal wiring layer is formed in a thickness so the smaller amount of radiating rays are irradiated to the regions except the region under the opening.

11. (Previously Presented) The semiconductor device in accordance with Claim 10, wherein an insulating layer is formed above the region irradiated, the opening being on the insulating layer.

12. (Previously Presented) The semiconductor device in accordance with Claim 11, wherein the metal wiring layer covers a part of the insulating layer.

13. (Previously Presented) The semiconductor device in accordance with Claim 12, wherein the semiconductor device is an insulated gate bipolar transistor, wherein the impurity region is a source region, and wherein the region irradiated is a positive-negative junction where a parasitic diode is generated.

Appl. No. 09/208105
Amdt. dated Mar. 16, 2004
Reply to Office action of Oct. 27, 2003

14. (Previously Presented) The semiconductor device in accordance with Claim 12, wherein the semiconductor device is a metal oxide semiconductor field effect transistor, wherein the impurity region is a source region, and wherein the region irradiated is a positive-negative junction region where a parasitic diode is generated.